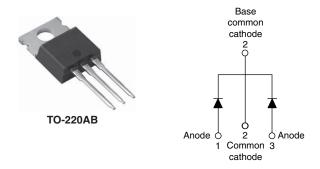




Vishay Semiconductors

Schottky Rectifier, 2 x 30 A



PRODUCT SUMMARY					
Package	TO-220AB				
I _{F(AV)}	2 x 30 A				
V _R	100 V				
V _F at I _F	0.69 V				
I _{RM} max.	20 mA at 125 °C				
T _J max.	175 °C				
Diode variation	Common cathode				
E _{AS}	11.25 mJ				

FEATURES

- 175 °C T_J operation
- Low forward voltage drop
- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance



- RoHS COMPLIANT HALOGEN FREE
- Guard ring for enhanced ruggedness and long term reliability
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according to JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)

DESCRIPTION

This center tap Schottky rectifier has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

MAJOR RATING	MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	CHARACTERISTICS	VALUES	UNITS					
I _{F(AV)}	Rectangular waveform (per device)	60	A					
V _{RRM}		100	V					
I _{FRM}	$T_C = 139 \ ^{\circ}C \ (per \ leg)$	60	A					
I _{FSM}	t _p = 5 μs sine	1500	~					
V _F	30 A _{pk} , T _J = 125 °C	0.69	V					
TJ	Range	- 65 to 175	°C					

VOLTAGE RATINGS						
PARAMETER	SYMBOL	VS-63CTQ100PbF	VS-63CTQ100-N3	UNITS		
Maximum DC reverse voltage	V _R	100	100	V		
Maximum working peak reverse voltage	V _{RWM}	100	100	v		

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	PARAMETER		TEST COND	TEST CONDITIONS				
Maximum averageper legforward currentper device			50 % duty cycle at $T_{e} = 120$ %	rootangular wayoform	30			
		I _{F(AV)}	50 % duty cycle at T_C = 139 °C, rectangular waveform		60			
Peak repetitive forward current per leg		I _{FRM}	Rated V _R , square wave, 20 kHz, T _C = 140 $^{\circ}$ C		60	А		
Maximum peak one cycle non-repetitive surge current per leg			5 μs sine or 3 μs rect. pulse	Following any rated load condition and with rated	1500			
		I _{FSM}	10 ms sine or 6 ms rect. pulse	V _{RRM} applied	300			
Non-repetitive avalanche energy per leg		E _{AS}	T _J = 25 °C, I _{AS} = 0.75 A, L = 40 mH		11.25	mJ		
Repetitive avalanche current pe	Repetitive avalanche current per leg		Current decaying linearly to zer Frequency limited by T_J maxim		0.75	А		

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VS-63CTQ100PbF, VS-63CTQ100-N3

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- 1	
- 1	
- 1	
- 1	ELECTRICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CO	NDITIONS	TYP.	MAX.	UNITS
		30 A	T 05 00	0.78	0.82	
Maximum forward voltage drop	V (1)	60 A	T _J = 25 °C	0.94	1.0	V
	V _{FM} ⁽¹⁾	30 A	T 405.00	0.64	0.69	
		60 A	T _J = 125 °C	0.78	0.83	
Maximum instantaneous reverse current	I _{RM}	T _J = 25 °C	Rated DC voltage	0.02	0.3	mA
Maximum instantaneous reverse current		T _J = 125 °C	haled DC vollage	11	20	
Maximum junction capacitance	CT	V_R = 5 V_{DC} (test signal range 100 kHz to 1 MHz) 25 °C		11	00	pF
Typical series inductance	L _S	Measured from top of terminal to mounting plane			.0	nH
Maximum voltage rate of change	dV/dt	Rated V _R	10 000		V/µs	

Note

 $^{(1)}\,$ Pulse width < 300 $\mu s,$ duty cycle < 2 $\,\%$

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	PARAMETER		TEST CONDITIONS	VALUES	UNITS		
Maximum junction and storage temperature range	je	T _J , T _{Stg}		- 65 to 175	°C		
Maximum thermal resistance junction to case per leg	,	R _{thJC}	DC operation	1.2	°C/W		
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.50	0/14		
Approximate weight				2	g		
Approximate weight				0.07	oz.		
Mounting torgue			Non-lubricated threads	6 (5)	kgf ⋅ cm		
Mounting torque -	maximum		Non-Inducated tilleads	12 (10)	(lbf ⋅ in)		
Marking device			Case style TO-220AB	63CT	Q100		



VS-63CTQ100PbF, VS-63CTQ100-N3

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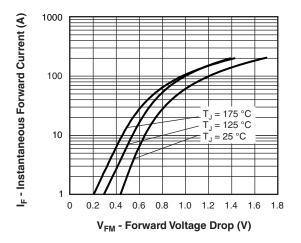


Fig. 1 - Maximum Forward Voltage Drop Characteristics

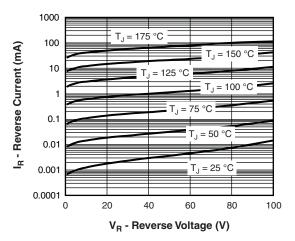


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

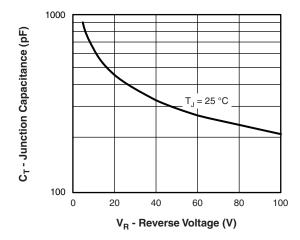


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

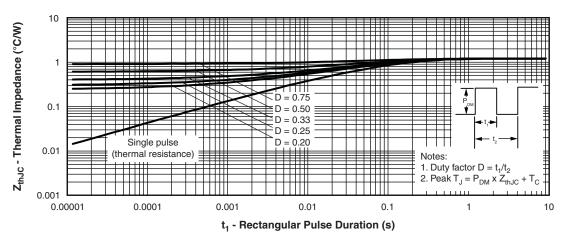


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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VS-63CTQ100PbF, VS-63CTQ100-N3

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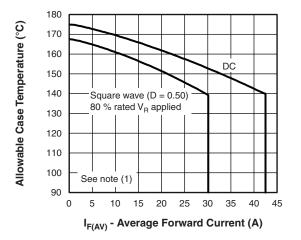
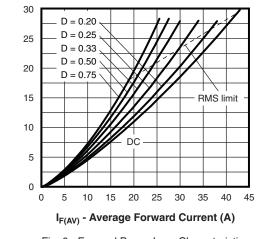
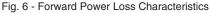
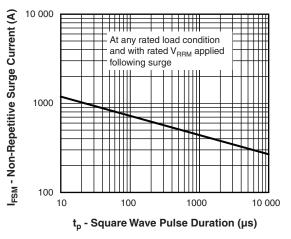


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current







Average Power Loss (W)

Fig. 7 - Maximum Non-Repetitive Surge Current (Per Leg)

Note

- ⁽¹⁾ Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$;
 - $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ \mathsf{x} \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see fig. 6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{80} \ \% \ \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$





Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code	VS-	63	С	т	Q	100	PbF
	1	2	3	4	5	6	7
1	-	Vishay	Semico	nductor	s produ	ct	
2	-	Curren	t rating	(60 A)			
3	-	Circuit	configui	ration			
		C = Co	mmon d	cathode			
4	-	Packag	je				
		T = TO	-220				
5	-	Schott	ky "Q" se	eries			
6	-	Voltage	e rating	(100 = 1	00 V)		
7	-	Enviro	nmental	digit			
		• PbF	= Lead	(Pb)-fre	e and R	oHS co	mpliant

• -N3 = Halogen-free, RoHS compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-63CTQ100PbF	50	1000	Antistatic plastic tube				
VS-63CTQ100-N3	50	1000	Antistatic plastic tube				

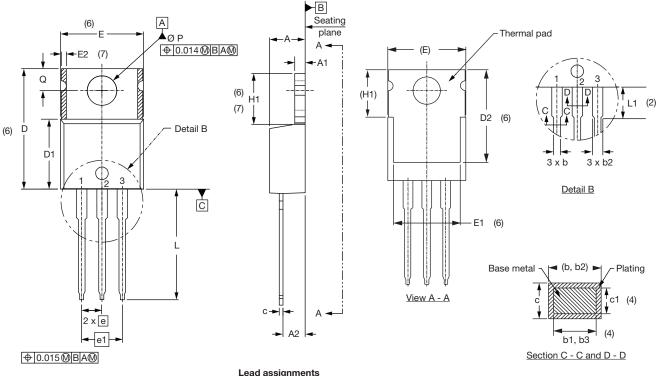
LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95222					
Part marking information	TO-220AB PbF	www.vishay.com/doc?95225			
	TO-220AB -N3	www.vishay.com/doc?95028			

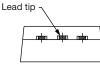


Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches





Leau	l as:	sign	me	пι
		-		

Diodes 1. - Anode/open

2. - Cathode 3. - Anode

	HES				
SYMBOL		IETERS	_	-	NOTES
	MIN.	MAX.	MIN.	MAX.	
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- ⁽³⁾ Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed $0.127 \text{ mm} (0.005^{\circ})$ per side. These dimensions are measured at the outermost extremes of the plastic body
- $^{\left(4\right) }$ Dimension b1, b3 and c1 apply to base metal only
- ⁽⁵⁾ Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° to 93°		

Conforms to JEDEC outline TO-220AB

- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- Outline conforms to JEDEC TO-220, except A2 (maximum) and (8) D2 (minimum) where dimensions are derived from the actual package outline

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